

IN THE CLAIMS

Please amend the claims as follows:

1. (currently amended) A quartz glass crucible for crystal pulling, said crucible comprising: a crucible wall, comprising an outer layer of opaque quartz glass and an inner layer, wherein the outer layer has an inner region and an outer region, said outer layer being provided with a crystallization promoter that effects crystallization of quartz glass with formation of a cristobalite when the quartz glass crucible is heated during said crystal pulling, wherein the crystallization promoter contains a first component other than silicon that acts in quartz glass as a network former or a network modifier and a second, alkali-metal-free component that acts in quartz glass as a breakpoint former, and wherein the outer layer has a doping region having a layer thickness of more than 0.2 mm and containing said components entrapped therein.
2. (previously presented) A quartz glass crucible according to claim 1, wherein the first component acts as a network former and contains a tetravalent substance.
3. (previously presented) A quartz glass crucible according to claim 2, wherein the tetravalent substance comprises one or more elements from the group consisting of titanium (Ti^{4+}), zirconium (Zr^{4+}), hafnium (Hf^{4+}), germanium (Ge^{4+}) and tin (Sn^{4+}).
4. (previously presented) A quartz glass crucible according to claim 1, wherein the second component contains a divalent substance that does not contain alkali metal.
5. (previously presented) A quartz glass crucible according to claim 4, wherein the divalent substance comprises one or more elements from the group consisting of barium (Ba^{2+}) and strontium.

6. (previously presented) A quartz glass crucible according to claim 1, wherein the first component and the second component each have a distribution coefficient in silicon of 10^{-5} or less.
7. (previously presented) A quartz glass crucible according to claim 1, wherein the first component and the second component are each contained in a concentration ranging from 0.003 mol-% to 0.02 mol-% in the doping region.
8. (previously presented) A quartz glass crucible according to claim 1, wherein the first component and the second component are contained in the doping region in the form of an oxide compound containing the said components.
9. (previously presented) A quartz glass crucible according to claim 8, wherein the oxide compound consists of a ternary oxide.
10. (previously presented) A quartz glass crucible according to claim 1, wherein the doping region has a layer thickness of more than 0.5 mm.
11. (previously presented) A quartz glass crucible according to claim 10, wherein the layer thickness is 10 mm or less.
12. (previously presented) A quartz glass crucible according to claim 1, wherein the quartz glass crucible has an essentially cylindrical side wall about the axis of rotation, and wherein the doping region is formed as a doping strip in the side wall.
13. (currently amended) A method for manufacturing a quartz glass crucible said method comprising producing a crucible base body comprising an outer layer of an opaque quartz glass and an inner layer, wherein at least part of the outer layer in an outer region surrounding an inner region is provided with a crystallization promoter which, on heating of the quartz glass

crucible during said crystal pulling, causes crystallization of quartz glass with formation of cristobalite, wherein a first component other than silicon that acts in quartz glass as a network former or as a network modifier, and an alkali-metal-free-second component acting as breakpoint former in quartz glass are used as to promote crystallization, and wherein said components are introduced into and entrapped in a doping region of the outer layer, said doping layer having a layer thickness of more than 0.2 mm.

14. (previously presented) A method according to claim 13, wherein the outer layer having the doping region is generated by introducing SiO_2 grains into a melting mold so as to be shaped therein into a crucible-shaped layer of SiO_2 grains, wherein said components are added to the SiO_2 grains before shaping of the doping region, and then the layer of SiO_2 grains is sintered so as to form the outer layer.
15. (previously presented) A method according to claim 13, wherein a tetravalent substance that acts as a network former is used as the first component.
16. (previously presented) A method according to claim 15, wherein the tetravalent substance comprises one or more elements selected from the group consisting of titanium (Ti^{4+}), zirconium (Zr^{4+}), hafnium (Hf^{4+}), germanium (Ge^{4+}) and tin (Sn^{4+}).
17. (previously presented) A method according to claim 13, wherein the second component contains a divalent substance that does not contain any alkali metal.
18. (previously presented) A method according to claim 17, wherein the divalent substance comprises one or more elements from the group consisting of barium (Ba^{2+}) and, strontium.

19. (previously presented) A method according to claim 1, wherein the first component and the second component are each introduced in a concentration ranging from 0.003 mol-% to 0.02 mol-% in the doping region.
20. (previously presented) A method according to claim 13, wherein the first component and the second component are contained in the doping region of the outer layer in the form of an oxide compound containing said components.
21. (previously presented) A method according to claim 20, wherein the oxide compound consists essentially of a ternary oxide.
22. (previously presented) A method according to claim 21, wherein the ternary oxide is barium titanate (BaTiO_3), barium zirconate (BaZrO_3), or a mixture thereof.
23. (previously presented) A quartz glass crucible according to claim 8, wherein the ternary oxide is barium titanate (BaTiO_3), barium zirconate (BaZrO_3), or a mixture thereof.
24. (previously presented) A quartz glass crucible according to claim 1, wherein the doping region has a layer thickness of more than 2 mm.
25. (previously presented) A quartz glass crucible according to claim 24, wherein the layer thickness is 10 mm or less.